Abstract

Method for producing a semiconductor wafer

A method for the simultaneous double-side polishing of a semiconductor wafer, which is situated in a carrier between an upper polishing plate covered with a first polishing pad and a lower polishing plate covered with a second polishing pad. Both polishing pads comprise abrasives of oxides of an element selected from the group consisting of silicon, aluminum and cerium, having an average size of 0.1 to 1.0 µm. A polishing agent solution is supplied during the polishing process, the pH value of which solution can be varied in a range of 11 to 13.5. A polishing agent solution having a pH of 11-12.5 is supplied in a first step and a polishing agent solution having a pH of greater than or equal to 13 is supplied in a second step.

Fig. 1